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## Patent Public Search | Text View

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United States Patent Application Publication

20250264676

Kind Code

A1

Publication Date

August 21, 2025

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### MANUFACTURING METHOD OF PACKAGE SUBSTRATE AND OPTICAL DEVICE

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#### Abstract

A manufacturing method of a package substrate includes providing a support structure; forming a first photo-sensitive layer over the support structure; patterning the first photo-sensitive layer to form first openings; curing the first photo-sensitive layer; and forming a functional structure in the first openings. An optical device is also provided.

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**Family ID:** 1000008475840

**Appl. No.:** 19/055507

**Filed:** February 18, 2025

#### Related U.S. Application Data

us-provisional-application US 63555082 20240218

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#### Publication Classification

**Int. Cl.:** G02B6/42 (20060101); H01L21/48 (20060101); H01L25/16 (20230101)

**U.S. Cl.:**

**CPC** G02B6/4246 (20130101); H01L21/486 (20130101); H01L25/167 (20130101);

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#### Background/Summary

CROSS-REFERENCE TO RELATED APPLICATION [0001] This application claims the priority benefit of the U.S. provisional application Ser. No. 63/555,082, filed on Feb. 18, 2024. The entirety of the above-mentioned patent application is hereby incorporated by reference herein and made a part of this specification.

## BACKGROUND

### Technical Field

[0002] The disclosure relates to a manufacturing method of package substrate and an optical device.

### Description of Related Art

[0003] With the vigorous development of the electronic industry, to achieve high density and high efficiency, various electronic products are becoming lighter, thinner, shorter, and smaller. For example, a thin and high-density package structure is usually expected to make an electronic product thinner. Therefore, with a decreasing semiconductor chip size and package structure size, how to develop a matching substrate without greatly increasing manufacturing costs has become an issue to be urgently resolved.

## SUMMARY

[0004] A manufacturing method of a package substrate includes providing a support structure; forming a first photo-sensitive layer over the support structure; patterning the first photo-sensitive layer to form first openings; curing the first photo-sensitive layer; and forming a functional structure in the first openings.

[0005] An optical device includes a package substrate including a first optical fiber array unit; a first transceiver disposed on and electrically connected to the package substrate; and a second transceiver disposed on and electrically connected to the package substrate. A first electrical signal and a first optical signal are transferred between the first transceiver and the second transceiver by the first optical fiber array unit. The first electrical signal and the first optical signal are converted by the first transceiver and the second transceiver.

[0006] To make the aforementioned more comprehensible, several embodiments accompanied with drawings are described in detail as follows.

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## Description

### BRIEF DESCRIPTION OF THE DRAWINGS

[0007] The accompanying drawings are included to provide a further understanding of the disclosure, and are incorporated in and constitute a part of this specification. The drawings illustrate exemplary embodiments of the disclosure and, together with the description, serve to explain the principles of the disclosure.

[0008] FIG. 1 to FIG. 5 are partial schematic cross-sectional views illustrating a manufacturing method of a package substrate according to some embodiments of the disclosure.

[0009] FIG. 6 is a partial schematic cross-sectional view illustrating a package substrate according to some embodiments of the disclosure.

[0010] FIG. 7 to FIG. 9 are partial schematic cross-sectional views illustrating a manufacturing method of a package substrate according to some embodiments of the disclosure.

[0012] FIG. 10 is a partial schematic cross-sectional view illustrating a package substrate according to some embodiments of the disclosure.

[0013] FIG. 11 is a flow diagram of some embodiments of a manufacturing method of a package substrate.

[0014] FIG. 12 is a partial schematic cross-sectional view illustrating an optical device according to some embodiments of the disclosure.

[0015] FIG. **13** is a partial schematic top view corresponding to FIG. **12**.

[0016] FIG. **14** and FIG. **15** are partial schematic cross-sectional views illustrating a package substrate according to some embodiments of the disclosure.

[0017] FIG. **16** is a partial schematic top view illustrating optical devices according to some embodiments of the disclosure.

[0018] FIG. **17** is a partial schematic cross-sectional view illustrating optical devices according to FIG. **16**.

## DESCRIPTION OF THE EMBODIMENTS

[0019] Exemplary embodiments of the disclosure are described below comprehensively with reference to the figures, but the disclosure may also be implemented in different ways and should not be construed as limited to the embodiments described herein. In the drawings, for the sake of clarity, the size and thickness of various regions, parts, and layers may not be drawn to actual scale. In order to facilitate understanding, the same elements in the following description are described with the same symbols.

[0020] The disclosure is more comprehensively described with reference to the figures of this embodiment. However, the disclosure may also be implemented in various different forms, and is not limited to the embodiments in the present specification. Thicknesses, dimensions, and sizes of layers or regions in the drawings are exaggerated for clarity. The same reference numbers are used in the drawings and the description to indicate the same or like parts, which are not repeated in the following embodiments.

[0021] Directional terms (for example, upper, lower, right, left, front, back, top, and bottom) used herein only refer to the graphical use, and are not intended to imply absolute orientation.

[0022] It should be understood that, although the terms “first”, “second”, “third”, or the like may be used herein to describe various elements, components, regions, layers, and/or portions, these elements, components, regions, and/or portions should not be limited by these terms. These terms are only used to distinguish one element, component, region, layer, or portion from another element, component, region, layer, or portion.

[0023] Unless otherwise defined, all terms (including technical and scientific terms) used herein have the same meaning as that commonly understood by one of ordinary skill in the art to which this disclosure belongs.

[0024] FIG. **1** to FIG. **5** are partial schematic cross-sectional views illustrating a manufacturing method of a package substrate according to some embodiments of the disclosure. FIG. **6** is a partial schematic cross-sectional view illustrating a package substrate according to some embodiments of the disclosure. In package substrate, requirements of a fine circuitry (may range from 0.4  $\mu\text{m}$  to 2  $\mu\text{m}$ ) are increasingly important and many problems are also derived. For example, conventional semi-additive processes are usually used to produce the fine circuitry, however, the etching of the seed layer is resulted to shrink and change in the conductive trace (such as copper trace) with removal seed layer, such that undesirable dimensional conductive trace may decrease the reliability of the package substrate. In the present disclosure at least illustrated in FIG. **1** to FIG. **5**, a photo-sensitive layer is used to create well-defined openings for embedded a circuit structure, by doing so, the circuit structure embedded in the photo-sensitive layer may be better retained in dimensions, thereby the reliability of the package substrate may be increased. In addition, the photo-sensitive layer may also reduce the manufacturing costs of the package substrate. Moreover, present patent applications integrate the electric and optical connections in one integrated optical electrical substrate.

[0025] Referring to FIG. **1**, a support structure **110** is provided. In some embodiments, the support structure **110** may be a circuit board having a conductive trace, for example, the support structure **110** may be a PCB substrate or the like, but the disclosure is not limited thereto. In other embodiments, the support structure **110** may be a dummy board free from the conductive trace, for example, the support structure **110** may be made of glass or other suitable materials, as long as the

materials may withstand the subsequent process and simultaneously support the overlying structure.

[0026] And then, at least one terminal **112** is formed on the support structure **110**. In some embodiments, the terminal **112** may be formed of copper, gold, nickel, aluminum, platinum, tin, combinations thereof, alloys thereof, or other suitable conductive materials by suitable depositing process on the support structure **110**, but the disclosure is not limited thereto. Here, the terminal **112** may be electrically connected or electrically isolated to the support structure **110** based on the requirements.

[0027] In the embodiment, a dielectric layer **120** is formed over the support structure **110**. For example, the dielectric layer **120** may be formed as follow. First, a photo-sensitive material (such as a photo-sensitive polyimide or the like) is deposited over the support structure **110**. In one embodiment, the photo-sensitive material may be formed in liquid form, but the disclosure is not limited thereto, in another embodiment, the photo-sensitive material may be formed in film form. And then, the photo-sensitive material is patterned to form at least one opening **10** (may be referred as via) to expose the terminal **112**. In some embodiments, a photolithography process including an exposure process and a development process and an etching process are used to pattern the photo-sensitive material. For example, the photolithography process may use a laser direct imaging tool or the like to well control a size of the opening **10**. Next, the photo-sensitive material is cured to form the dielectric layer **120**. In some embodiments, a thickness **120T** of the dielectric layer **120** may be 10 micrometers ( $\mu\text{m}$ ) or other suitable values.

[0028] Referring to FIG. 2, a photo-sensitive layer **130** is formed over the support structure **110**. For example, the photo-sensitive layer **130** (such as a photo-sensitive polyimide or the like) is deposited on the dielectric layer **120** and in the opening **10**. In this step, the photo-sensitive layer **130** may be formed in liquid form, but the disclosure is not limited thereto, the photo-sensitive layer **130** also may be formed in film form. In some embodiments, a thickness **130T** of the photo-sensitive layer **130** over the dielectric layer **120** is thinner than the thickness **120T** of the dielectric layer **120**, for example, a thickness **130T** of the photo-sensitive layer **130** may be 5 micrometers ( $\mu\text{m}$ ) or other suitable values.

[0029] Referring to FIG. 3, the photo-sensitive layer **130** is patterned to form an opening **20** (may be referred another via) exposing the terminal **112** and a plurality of openings **30** (may be referred as trenches) exposing a top surface **120t** of the dielectric layer **120**, in this way, different depths of the openings are formed in the photo-sensitive layer **130**. For example, a depth **20d** of the opening **20** is deeper than a depth **30d** of the opening **30**. Further, a size of the opening **20** may be bigger than or smaller than a size of the opening **10**. Here, the size may be diameter or the like. Moreover, materials of the dielectric layer **120** may be same as materials of the photo-sensitive layer **130**, but the disclosure is not limited thereto, materials of the dielectric layer **120** may also be different from materials of the photo-sensitive layer **130** based on the design requirement.

[0030] In the embodiments, a photolithography process including an exposure process and a development process and an etching process are used to pattern the photo-sensitive layer **130**. For example, stepper exposure may be used to achieve different depths of the openings (the opening **20** and the opening **30**) by using different photomasks (not shown), but the disclosure is not limited thereto. In some embodiments, the laser direct imaging (LDI) is used to expose the deeper opening **20** with higher energy and expose the shallow openings **30** with lower energy, thereby the photomasks may be omitted.

[0031] Referring to FIG. 4 and FIG. 5, the photo-sensitive layer **130** is cured. Next, a circuit structure **140** is formed in the opening **20** and the openings **30**, wherein the circuit structure **140** may be a functional structure. In the embodiment, the circuit structure **140** is manufactured as follow. In FIG. 4, a seed layer **141** is formed over the support structure **110**, wherein the seed layer **141** includes a seed via portion **141a** formed in the opening **20** and seed trench portions **141b** formed in the openings **30**. In some embodiments, the seed layer **141** is conformally formed by

sputtering with Ti/Cu. And then, a conductive layer **142** is formed on the seed layer **141**, wherein the conductive layer **142** includes a conductive via portion **142a** formed on the seed via portion **141a** of the seed layer **141** and conductive trench portions **142b** formed on the seed trench portions **141b** of the seed layer **141**. Next, in FIG. 5, a planarization process is performed, such that a top surface **130t** of the photo-sensitive layer **130** is coplanar with a top surface of the circuit structure **140** (such as a top surface **141t** of the seed layer **141** and a top surface **142t** of the conductive layer **142**). Here, the planarization process may include CMP, grinding, chemical etching, or a combination thereof. The manufacturing of a package substrate **100** is roughly completed via the above steps.

[0032] On the other hand, when the support structure **110** is the circuit board, the support structure **110** is not removed after forming the circuit structure **140**, in contrast, when the support structure **110** is the dummy board, the support structure **110** is removed after forming the circuit structure **140**.

[0033] It should be noted that the package substrate **100** having two layers is an example for illustrating, numbers of the package substrate **100** may be not limited, that is to say, in another embodiment, as shown in FIG. 6, for higher integrating, another dielectric layer **120**, another photo-sensitive layer **130**, and another circuit structure **140** may be formed by similar method in FIG. 1 to FIG. 5 on the support structure **110** to constitute a package substrate **100A**. In yet another embodiment (not shown), the dielectric layer **120** may be omitted, that is to say, only the photo-sensitive layer **130** and the circuit structure **140** are direct in contact with the support structure **110** and the terminal **112** respectively.

[0034] FIG. 7 to FIG. 9 are partial schematic cross-sectional views illustrating a manufacturing method of a package substrate according to some embodiments of the disclosure. FIG. 10 is a partial schematic cross-sectional view illustrating a package substrate according to some embodiments of the disclosure. In package substrate, an optical application is another issue and many problems are also derived. For example, as the demanding calculation power of artificial intelligence increases, the bandwidth of communication between chips also increases. However, the communication bandwidth is limited. In the present disclosure at least illustrated in FIG. 7 to FIG. 9, a photo-sensitive layer is used to create well-defined openings for embedded optical structure in the package substrate. To be specific, it may create higher quality multiple channels to increase the density of optical fiber array unit in the package substrate, thereby the communication bandwidth may be improved. In addition, the photo-sensitive layer may also reduce the manufacturing costs of the package substrate.

[0035] Referring to FIG. 7 to FIG. 8, similar to FIG. 1 to FIG. 3, the same reference numbers are used in the drawings and the description to indicate the same or like parts, which are not repeated in the following embodiments. The support structure **110** is provided. And then, the dielectric layer **120** is formed over the support structure **110**. Next, the photo-sensitive layer **130** is formed over the support structure **110** and the photo-sensitive layer **130** is patterned to form the openings **30**. To be specific, based on different functionalities in the package substrate, the opening **10** in FIG. 1 and the opening **20** in FIG. 2 are omitted in this embodiment.

[0036] Referring to FIG. 8 to FIG. 9, an optical structure **240** is formed in the openings **30**, wherein the optical structure **240** may be a functional structure. In the embodiment, the optical structure **240** is manufactured as follow. In FIG. 8, the optical structure **240** is formed on the photo-sensitive layer **130** and in the openings **30** by suitable deposition method. Next, in FIG. 9, a planarization process is performed, such that a top surface **130t** of the photo-sensitive layer **130** is coplanar with a top surface **240t** of the optical structure **240**. Here, the planarization process may include CMP, grinding, chemical etching, or a combination thereof. The manufacturing of a package substrate **200** is roughly completed via the above steps.

[0037] In the embodiment, a refractive index of the dielectric layer **120** is smaller than a refractive index of the optical structure **240**, such that the dielectric layer **120**, the photo-sensitive layer **130**,

and the optical structure **240** are configured to an optical fiber array unit to let light pass through thereof. Here, materials of the optical structure **240** may be any suitable optical materials as long as the refractive index thereof is greater than the dielectric layer **120** and transparent that can transmit light in visible and/or infrared range.

[0038] It should be noted that the package substrate **200** having two layers is an example for illustrating, numbers of the package substrate **200** may be not limited, that is to say, in another embodiment, as shown in FIG. **10**, for higher integrating, another two dielectric layer **120**, another photo-sensitive layer **130**, another optical structure **240** may be formed by similar method in FIG. **7** to FIG. **9** on the support structure **110** to constitute a package substrate **200A**.

[0039] FIG. **11** is a flow diagram of some embodiments of a manufacturing method of a package substrate. The method includes a number of operations (blocks **S101**, **S102**, **S103**, **S104**, and **S105**). The description and illustration are not deemed as a limitation to the sequence of the operations.

[0040] At block **S101**, a support structure is provided. At block **S102**, a photo-sensitive layer is over the support structure. At block **S103**, the photo-sensitive layer is patterned to form openings. At block **S104**, the photo-sensitive layer is cured. FIG. **1** to FIG. **4** illustrate cross-sectional views of some embodiments corresponding to blocks **S101**, **S102**, **S103**, and **S104**, meanwhile FIG. **7** to FIG. **8** also illustrate cross-sectional views of some embodiments corresponding to blocks **S101**, **S102**, **S103** and **S104**.

[0041] At block **S105**, a functional structure is formed in the openings. FIG. **4** illustrates a cross-sectional view of some embodiments corresponding to block **S105**, meanwhile FIG. **8** illustrates a cross-sectional view of some embodiments corresponding to block **S105**.

[0042] FIG. **12** is a partial schematic cross-sectional view illustrating an optical device according to some embodiments of the disclosure. FIG. **13** is a partial schematic top view corresponding to FIG. **12**. FIG. **14** and FIG. **15** are partial schematic cross-sectional views illustrating a package substrate according to some embodiments of the disclosure. In the present disclosure, the package substrate **200B** including the optical fiber array unit may be further used to constitute an optical device **300** for reducing energy consumption. Here, the package substrate **200B** in FIG. **12** is similar to the package substrate **200A** in FIG. **10** and the difference therebetween is the optical structure **240** is further extending to a top surface **120t** of the dielectric layer **120** and a plurality of mirror **201** are optionally formed on the optical structure **240** to reflect the light in the package substrate **200B**.

[0043] In the embodiment, the optical device **300** further includes a transceiver **310** and a transceiver **320** disposed on and electrically connected to the package substrate **200B** respectively. To be specific, the package substrate **200B** includes two set of the optical fiber array units (including two optical structure **240**), wherein electrical signals and optical signals are transferred between the transceiver **310** and the transceiver **320** by two set of the optical fiber array units of the package substrate **200B**, and the electrical signals and the optical signals are converted by the transceiver **310** and the transceiver **320**, that is to say, there are two light path in the package substrate **200B** provided by the two set of the optical fiber array units, therefore, the optical device **300** may be referred as a co-packaged optical (CPO) device.

[0044] In some embodiments, the transceiver **310** and/or the transceiver **320** is an array structure. For example, the transceiver **310** and/or the transceiver **320** includes a micro-LED array with lens providing electrical to optical (E/O) conversion, a photo diode array providing optical to electrical (O/E) conversion, or the like. Moreover, the transceiver **310** and the transceiver **320** may be connected to the package substrate **200B** through a plurality of connectors **301**.

[0045] In some embodiments, the transceiver **310** is electrically connected to a processor chip **311**, and the transceiver **320** is electrically connected to a memory chip **321**. Further, a plurality of connection lines CL may be formed, wherein one of connection lines CL is located between the transceiver **310** and the processor chip **311** and another one of connection lines CL is located between the transceiver **320** and the memory chip **321** for electrical connection.

[0046] The package substrate may have various alternative implementation in different design

requirements. For example, In FIG. 14, the package substrate **400** is constituted by stacking the package substrate **100A** and the package substrate **200B** in a vertical direction. On the other hand, in FIG. 15, the package substrate **400A** is constituted by arranging the package substrate **100A** and the package substrate **200B** side by side.

[0047] FIG. 16 is a partial schematic top view illustrating optical devices according to some embodiments of the disclosure. FIG. 17 is a partial schematic cross-sectional view illustrating optical devices according to FIG. 16. The optical device **300** may have various alternative implementation in different design requirements. In FIG. 16 and FIG. 17, multiple processor chips **311** (such as XPU) may constitute to a sea of processor chip unit **311A**, multiple memory chips **321** (such as HBM) may constitute to a sea of memory chip unit **321A**, and the sea of processor chip unit **311A** may be electrically connected to sea of memory chip unit **321A** by the optical device **300**, wherein the sea of processor chip unit **311A** and the sea of memory chip unit **321A** are disposed on a circuit board **340**. Here, the sea of processor chip unit **311A** includes connection component **302** embedded in the substrate **311** (localized interconnection such as silicon bridge as shown in FIG. 17) and L3 cache **303** bonded to the processor **311** for high bandwidth communication, but the disclosure is not limited thereto. In addition, a net-work switching chip **350** disposed beside the circuit board **340** is provided. The net-work switching chip **350** may be electrically connected to the circuit board **340** by the optical device **300**. In some embodiments, one of the transceiver **310** and the transceiver **320** is optionally further electrically connected to a HPC module.

[0048] It will be apparent to those skilled in the art that various modifications and variations can be made to the disclosed embodiments without departing from the scope or spirit of the disclosure. In view of the foregoing, it is intended that the disclosure covers modifications and variations provided that they fall within the scope of the following claims and their equivalents.

## Claims

1. A manufacturing method of a package substrate, comprising: providing a support structure; forming a first photo-sensitive layer over the support structure; patterning the first photo-sensitive layer to form first openings; curing the first photo-sensitive layer; and forming a functional structure in the first openings.
2. The manufacturing method of a package substrate according to claim 1, wherein the first photo-sensitive layer comprises photo-sensitive polyimide.
3. The manufacturing method of a package substrate according to claim 1, further comprising: performing a photolithography process and an etching process to pattern the first photo-sensitive layer.
4. The manufacturing method of a package substrate according to claim 3, wherein the photolithography process comprises using photomasks or using a laser direct imaging tool.
5. The manufacturing method of a package substrate according to claim 1, further comprising: performing a planarization process after forming the functional structure, such that a top surface of the first photo-sensitive layer is coplanar with a top surface of the functional structure.
6. The manufacturing method of a package substrate according to claim 1, wherein the support structure has a conductive trace, and the support structure is not removed after forming the functional structure.
7. The manufacturing method of a package substrate according to claim 1, wherein the support structure is free from a conductive trace, and the support structure is removed after forming the functional structure.
8. The manufacturing method of a package substrate according to claim 1, wherein the functional structure is a circuit structure.
9. The manufacturing method of a package substrate according to claim 8, wherein a manufacturing

method of the circuit structure comprising: forming a seed layer over the support structure by sputtering with Ti/Cu; and forming a conductive layer on the seed layer by plating with Cu.

**10.** The manufacturing method of a package substrate according to claim 8, wherein the first openings have different depths.

**11.** The manufacturing method of a package substrate according to claim 1, wherein the functional structure is an optical structure.

**12.** The manufacturing method of a package substrate according to claim 11, further comprising: forming a second photo-sensitive layer between the support structure and the first photo-sensitive layer; and curing the second photo-sensitive layer to form a second photo-sensitive layer, wherein a refractive index of the second photo-sensitive layer is smaller than a refractive index of the optical structure, such that the first photo-sensitive layer, the second photo-sensitive layer, and the optical structure are configured to an optical fiber array unit.

**13.** An optical device, comprising: a package substrate comprising a first optical fiber array unit; a first transceiver disposed on and electrically connected to the package substrate; and a second transceiver disposed on and electrically connected to the package substrate, wherein: a first electrical signal and a first optical signal are transferred between the first transceiver and the second transceiver by the first optical fiber array unit; and the first electrical signal and the first optical signal are converted by the first transceiver and the second transceiver.

**14.** The optical device according to claim 13, wherein the first optical fiber array unit comprises a first photo-sensitive layer, a second photo-sensitive layer disposed on the first photo-sensitive layer, and a first optical structure embedded in the second photo-sensitive layer.

**15.** The optical device according to claim 13, wherein: the package substrate further comprising: a second optical fiber array unit; a second electrical signal and a second optical signal are transferred between the first transceiver and the second transceiver by the second optical fiber array unit; and the second electrical signal and the second optical signal are converted by the first transceiver and the second transceiver.

**16.** The optical device according to claim 15, wherein the second optical fiber array unit comprises a third photo-sensitive layer disposed on the first optical fiber array unit, a fourth photo-sensitive layer disposed on the third photo-sensitive layer, and a second optical structure embedded in the fourth photo-sensitive layer.

**17.** The optical device according to claim 13, wherein the package substrate further comprising: a circuit unit comprising a fifth photo-sensitive layer underlying or located beside the first optical fiber array unit and a circuit structure embedded in the fifth photo-sensitive layer.

**18.** The optical device according to claim 13, wherein one of the first transceiver and the second transceiver is electrically connected to a processor chip, and another one of the first transceiver and the second transceiver is electrically connected to a memory chip.

**19.** The optical device according to claim 13, wherein one of the first transceiver and the second transceiver is further electrically connected to a HPC module.

**20.** The optical device according to claim 13, wherein the first transceiver and/or the second transceiver is an array structure.

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